

**30V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET** 

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C		
30V	24mΩ @ V <sub>GS</sub> = 10V	7.2A		
	36mΩ @ V <sub>GS</sub> = 4.5V	5.8A		

# **Description and Applications**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

#### **Features and Benefits**

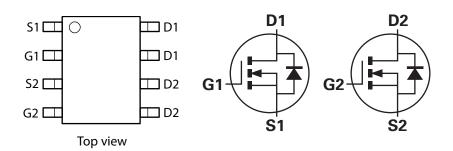
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)

## **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



TOP VIEW



## Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3024LSD-13	N3024LD	13	12	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## **Marking Information**



N3024LD = Product Type Marking Code D11 = Manufacturer's Marking YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)



#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V <sub>DSS</sub>	30	V
Gate-Source voltage			V <sub>GS</sub>	±20	V
Continuous Drain current		(Notes 3 & 5)	I <sub>D</sub>	7.2	
	V <sub>GS</sub> = 10V	T <sub>A</sub> = 70°C (Notes 3 & 5)		5.8	٨
	$v_{GS} = 10v$	(Notes 2 & 5)		5.7	A
		(Notes 2 & 6)		6.8	
Pulsed Drain current	V <sub>GS</sub> = 10V	(Notes 4 & 5)	I <sub>DM</sub>	34	A
Continuous Source current (Body diode) (No		(Notes 3 & 5)	IS	3.3	A
Pulsed Source current (Body diode) (Notes 4 & 5)		(Notes 4 & 5)	I <sub>SM</sub>	34	A

# Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Notes 2 & 5)		1.3 10.0		
Power dissipation Linear derating factor	(Notes 2 & 6)	P <sub>D</sub>	1.8 14.3	W mW/°C	
	(Notes 3 & 5)		2.0 15.9		
Thermal Resistance, Junction to Ambient	(Notes 2 & 5) (Notes 2 & 6) (Notes 3 & 5)	R <sub>θJA</sub>	100 70 63	°C/W	
Thermal Resistance, Junction to Lead	(Notes 5 & 7)	R <sub>0JL</sub>	53	°C/W	
Operating and storage temperature range		TJ, TSTG	-55 to 150	°C	

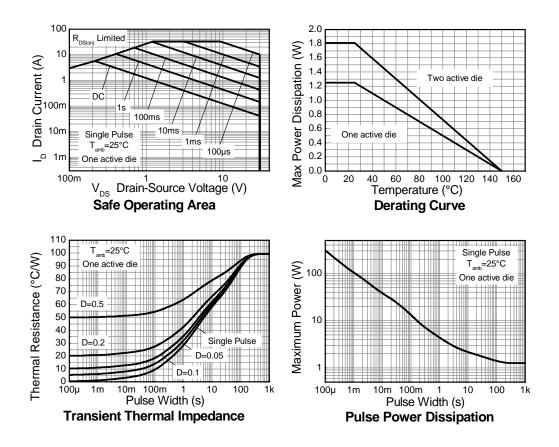
Notes: 2. For a device surface mounted on 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

3. Same as note (2), except the device is measured at  $t \le 10$  sec. 4. Same as note (2), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature. 5. For a dual device with one active die. 6. For a device with two active die running at equal power.

7. Thermal resistance from junction to solder-point (at the end of the drain lead): the device is operating in a steady-state condition.



# **Thermal Characteristics**





DMN3024LSD

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS	•				•••••	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		0.5	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0		3.0	V	I <sub>D</sub> = 250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 8)	Р			0.024	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.0A
Static Drain-Source On-Resistance (Note 6)	R <sub>DS (ON)</sub>	_		0.036	12	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.0A
Forward Transconductance (Notes 8 & 9)	<b>g</b> fs		16.5	_	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 7.1A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	_	0.82	1.2	V	I <sub>S</sub> = 1.7A, V <sub>GS</sub> = 0V
Reverse recovery time (Note 9)	t <sub>rr</sub>		12	—	ns	
Reverse recovery charge (Note 9)	Q <sub>rr</sub>	_	4.8	_	nC	I <sub>S</sub> = 2.2A, di/dt= 100A/μs
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	_	608	—	pF	
Output Capacitance	C <sub>oss</sub>	_	132	_	pF	<sup>─</sup> V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V −f= 1MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	71	_	pF	
Total Gate Charge	Qg	_	6.3	_	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 7A
Total Gate Charge	Qg	_	12.9	_	nC	
Gate-Source Charge	Q <sub>gs</sub>	_	2.5	_	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V
Gate-Drain Charge	Q <sub>gd</sub>	_	2.5	_	nC	$-I_{D}=7A$
Turn-On Delay Time (Note 10)	t <sub>D(on)</sub>	_	2.9	_	ns	
Turn-On Rise Time (Note 10)	tr	_	3.3		ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V
Turn-Off Delay Time (Note 10)	t <sub>D(off)</sub>	_	16		ns	I <sub>D</sub> = 1A, R <sub>G</sub> ≅ 6.0Ω
Turn-Off Fall Time (Note 10)	tf	_	8	_	ns	1

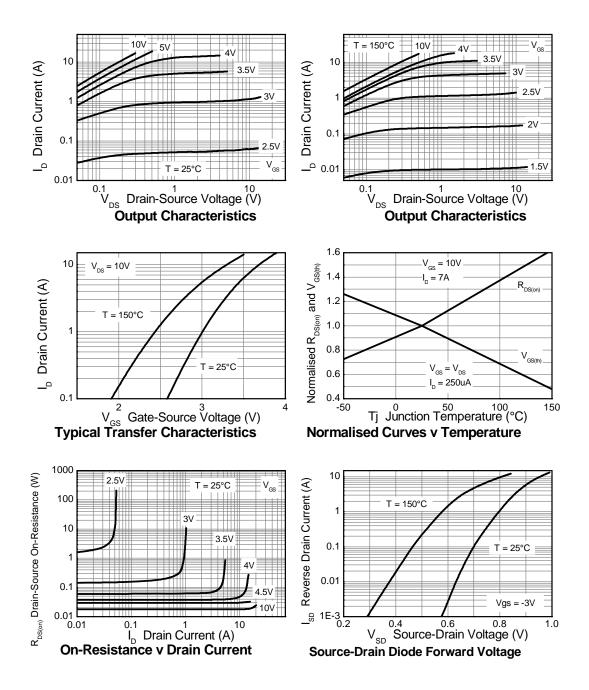
8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%$ Notes:

For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperatures.



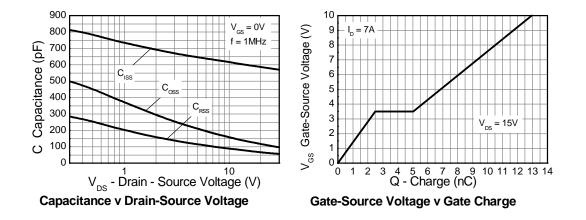


# **Typical Characteristics**

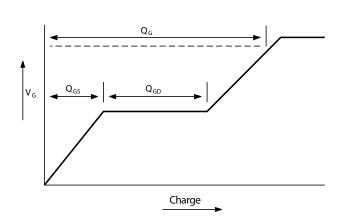




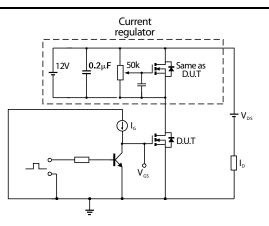
# **Typical Characteristics - continued**



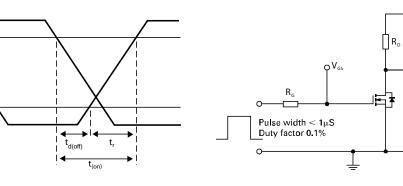
**Test Circuits** 



Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

Switching time test circuit

V<sub>DS</sub> 90%

10% V<sub>GS</sub>

t<sub>d(on)</sub>

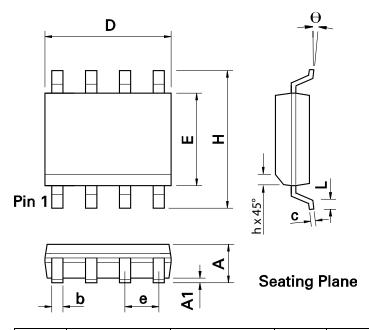
t<sub>r</sub>

 $V_{\rm dd}$ 

-0V<sub>DS</sub>

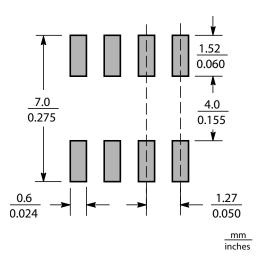


# **Package Outline Dimensions**



DIM	Inc	hes	Millin	neters	DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
А	0.053	0.069	1.35	1.75	е	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	С	0.008	0.010	0.19	0.25
Н	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

# Suggested Pad Layout





#### DMN3024LSD

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